

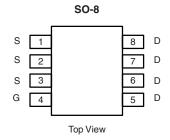
P-Channel 30-V (D-S) MOSFET

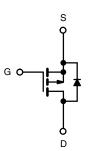
PRODUCT SUMMARY				
V _{DS} (V)	$R_{DS(on)}\left(\Omega\right)$	I _D (A)		
	$0.042 \text{ at V}_{GS} = -10 \text{ V}$	- 5.7		
- 30	0.055 at V _{GS} = - 6 V	- 5.0		
	0.070 at V _{GS} = - 4.5 V	- 4.4		

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- Compliant to RoHS Directive 2002/95/EC







P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS	A = 25 °C, unle	ss otherwise n	oted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V _{DS}	- 30		V
Gate-Source Voltage		V _{GS}	± 20		
Continuous Dunis Comment /T 150 90\8	T _A = 25 °C	1	- 5.7 - 4.1	- 4.1	^
Continuous Drain Current (T _J = 150 °C) ^a	T _A = 70 °C	I _D	- 4.6	- 3.2	
Pulsed Drain Current		I _{DM}	- 30		Α
Continuous Source Current (Diode Conduction) ^a		I _S	- 2.3	- 1.1	
	T _A = 25 °C	P _D	2.5	1.3	W
Maximum Power Dissipation ^a	T _A = 70 °C	T D	1.6	0.8]
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Mariana landia la Andria d	t ≤ 10 s	R	40	50	
Maximum Junction-to-Ambient ^a	Steady State	R_{thJA}	70	95	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R _{thJF}	24	30	

Notes:

a. Surface Mounted on 1" x 1" FR4 board.



Parameter	Symbol	Test Conditions		Typ. ^a	Max.	Unit	
Static							
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \mu A$	- 1.0		- 3.0	V	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA	
Zava Cata Valtana Duain Comunit	l	V _{DS} = - 30 V, V _{GS} = 0 V			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = - 30 V, V _{GS} = 0 V, T _J = 70 °C			- 5	- μΑ	
On-State Drain Current ^b	1-7	$V_{DS} \le -10 \text{ V}, V_{GS} = -10 \text{ V}$	- 20			A	
	I _{D(on)}	$V_{DS} \le -5 \text{ V}, V_{GS} = -4.5 \text{ V}$	- 5				
		V _{GS} = - 10 V, I _D = - 5.7 A		0.033	0.042		
Drain-Source On-State Resistance ^b	R _{DS(on)}	V _{GS} = - 6 V, I _D = - 5 A		0.043	0.055	Ω	
		V _{GS} = - 4.5 V, I _D = - 4.4 A		0.056	0.070		
Forward Transconductance ^b	9 _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -5.7 \text{ A}$		13		S	
Diode Forward Voltage ^b	V_{SD}	$I_S = -2.3 \text{ A}, V_{GS} = 0 \text{ V}$		- 0.8	- 1.1	V	
Dynamic ^a							
Total Gate Charge	Q_g			16	24		
Gate-Source Charge	Q_{gs}	$V_{DS} = -15 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -3.5 \text{ A}$		2.3		nC	
Gate-Drain Charge	Q_{gd}			4.5			
Gate Resistance	R_{g}			8.8		Ω	
Turn-On Delay Time	t _{d(on)}			14	25		
Rise Time	t _r	V_{DD} = - 15 V, R_L = 15 Ω		14	25	ns	
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ - 1 A, $V_{GEN}=$ - 10 V, $R_g=6~\Omega$		42	70		
Fall Time	t _f			30	50		
Source-Drain Reverse Recovery Time	t _{rr}	I _F = - 1.2 A, dI/dt = 100 A/μs		30	60		

Notes:

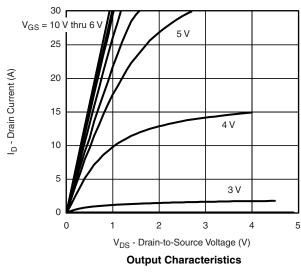
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

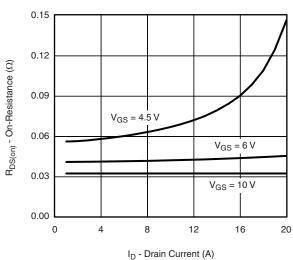
a. Guaranteed by design, not subject to production testing.

b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$

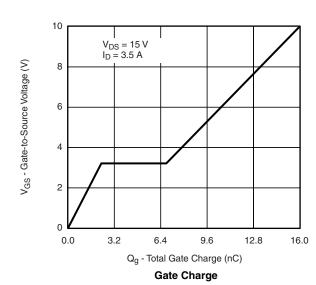


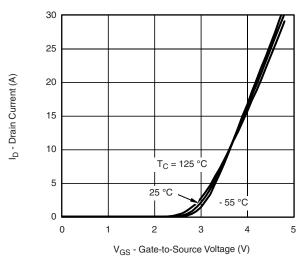
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



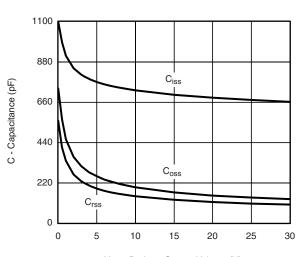


On-Resistance vs. Drain Current



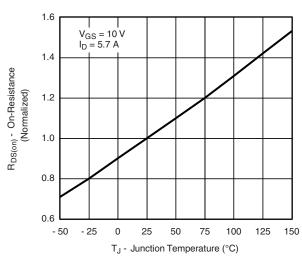


Transfer Characteristics



V_{DS} - Drain-to-Source Voltage (V)

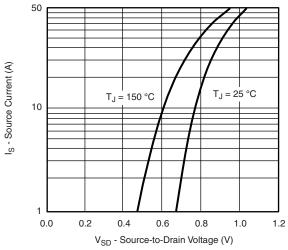




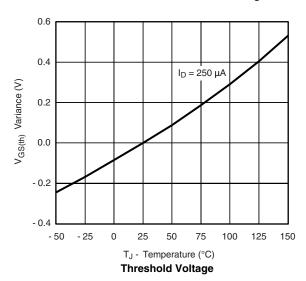
On-Resistance vs. Junction Temperature



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

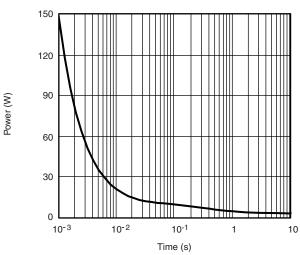


Source-Drain Diode Forward Voltage

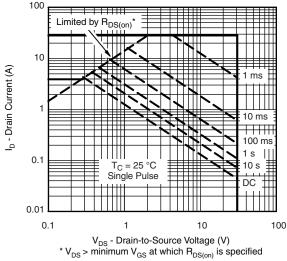


0.20 0.16 R_{DS(on)} - On-Resistance (Ω) $I_D = 5.7 \text{ A}$ 0.12 0.08 0.04 0.00 0 10 V_{GS} - Gate-to-Source Voltage (V)

On-Resistance vs. Gate-to-Source Voltage



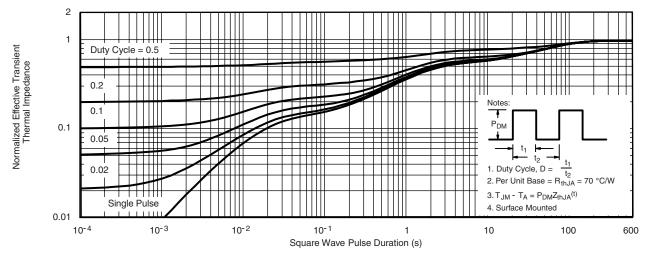
Single Pulse Power, Junction-to-Ambient



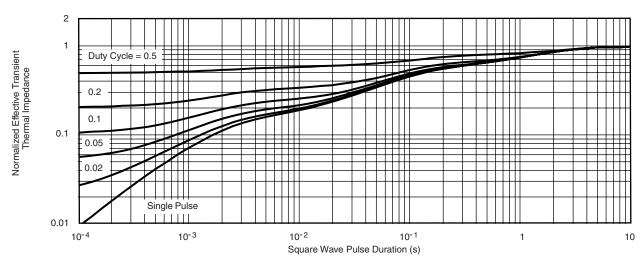
Safe Operating Area, Junction-to-Foot



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



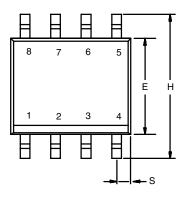
Normalized Thermal Transient Impedance, Junction-to-Ambient

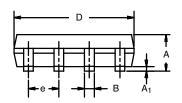


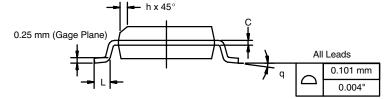
Normalized Thermal Transient Impedance, Junction-to-Foot



SOIC (NARROW): 8-LEAD JEDEC Part Number: MS-012





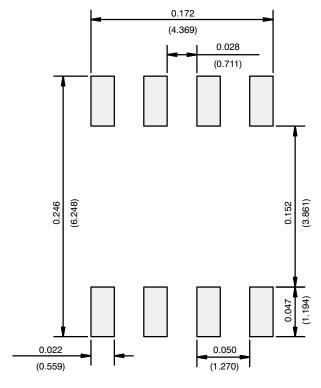


	MILLIM	IETERS	INCHES			
DIM	Min	Max	Min	Max		
Α	1.35	1.75	0.053	0.069		
A ₁	0.10	0.20	0.004	0.008		
В	0.35	0.51	0.014	0.020		
С	0.19	0.25	0.0075	0.010		
D	4.80	5.00	0.189	0.196		
E	3.80	4.00	0.150	0.157		
е	1.27	BSC	0.050 BSC			
Н	5.80	6.20	0.228	0.244		
h	0.25	0.50	0.010	0.020		
L	0.50	0.93	0.020	0.037		
q	0°	8°	0°	8°		
S	0.44	0.64	0.018	0.026		
ECN: C-06527-Rev. I, 11-Sep-06						

DWG: 5498

APPLICATION NOTE

RECOMMENDED MINIMUM PADS FOR SO-8



Recommended Minimum Pads Dimensions in Inches/(mm)

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